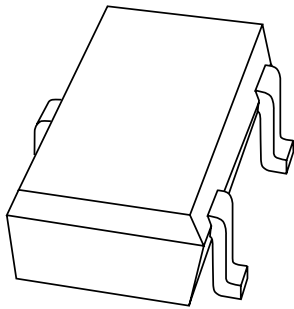


DATA SHEET



Datasheet.Live

PMSTA42; PMSTA43 NPN high-voltage transistors

Product data sheet
Supersedes data of 1997 Jun 19

1999 May 21

NPN high-voltage transistors

PMSTA42; PMSTA43

FEATURES

- High current (max. 500 mA)
- High voltage (max. 200 V).

APPLICATIONS

- High-voltage switching in telephony applications.

DESCRIPTION

NPN high-voltage transistor in a SOT323 plastic package.
PNP complements: PMSTA92 and PMSTA93.

MARKING

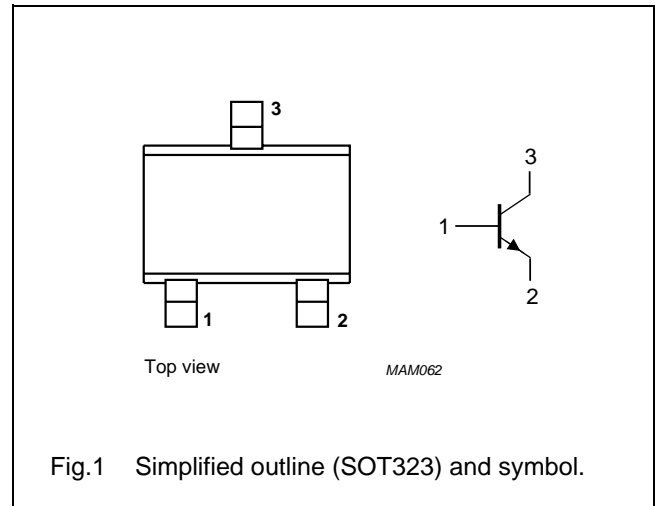
TYPE NUMBER	MARKING CODE ⁽¹⁾
PMSTA42	*1D
PMSTA43	*1E

Note

- * = - : Made in Hong Kong.
* = t : Made in Malaysia.

PINNING

PIN	DESCRIPTION
1	base
2	emitter
3	collector



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter			
	PMSTA42		–	300	V
	PMSTA43		–	200	V
V_{CEO}	collector-emitter voltage	open base			
	PMSTA42		–	300	V
	PMSTA43		–	200	V
V_{EBO}	emitter-base voltage	open collector	–	6	V
I_C	collector current (DC)		–	100	mA
I_{CM}	peak collector current		–	200	mA
I_{BM}	peak base current		–	100	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25\text{ °C}$; note 1	–	200	mW
T_{stg}	storage temperature		–65	+150	°C
T_j	junction temperature		–	150	°C
T_{amb}	operating ambient temperature		–65	+150	°C

Note

1. Transistor mounted on an FR4 printed-circuit board.

NPN high-voltage transistors

PMSTA42; PMSTA43

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-a}$	thermal resistance from junction to ambient	note 1	625	K/W

Note

1. Transistor mounted on an FR4 printed-circuit board.

CHARACTERISTICS

$T_{amb} = 25\text{ °C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I_{CBO}	collector cut-off current				
	PMSTA42	$I_E = 0; V_{CB} = 200\text{ V}$	–	100	nA
	PMSTA43	$I_E = 0; V_{CB} = 160\text{ V}$	–	100	nA
I_{EBO}	emitter cut-off current				
	PMSTA42	$I_C = 0; V_{EB} = 6\text{ V}$	–	100	nA
	PMSTA43	$I_C = 0; V_{EB} = 4\text{ V}$	–	100	nA
h_{FE}	DC current gain	$I_C = 1\text{ mA}; V_{CE} = 10\text{ V}$	25	–	
		$I_C = 10\text{ mA}; V_{CE} = 10\text{ V}$	40	–	
		$I_C = 30\text{ mA}; V_{CE} = 10\text{ V};$ note 1	40	–	
V_{CEsat}	collector-emitter saturation voltage	$I_C = 20\text{ mA}; I_B = 2\text{ mA}$	–	500	mV
C_{re}	feedback capacitance	$I_C = i_c = 0; V_{CB} = 20\text{ V}; f = 1\text{ MHz}$			
	PMSTA42		–	3	pF
	PMSTA43		–	4	pF
f_T	transition frequency	$I_C = 10\text{ mA}; V_{CE} = 20\text{ V}; f = 100\text{ MHz}$	50	–	MHz

Note

1. Pulse test: $t_p \leq 300\text{ }\mu\text{s}; \delta \leq 0.02$.

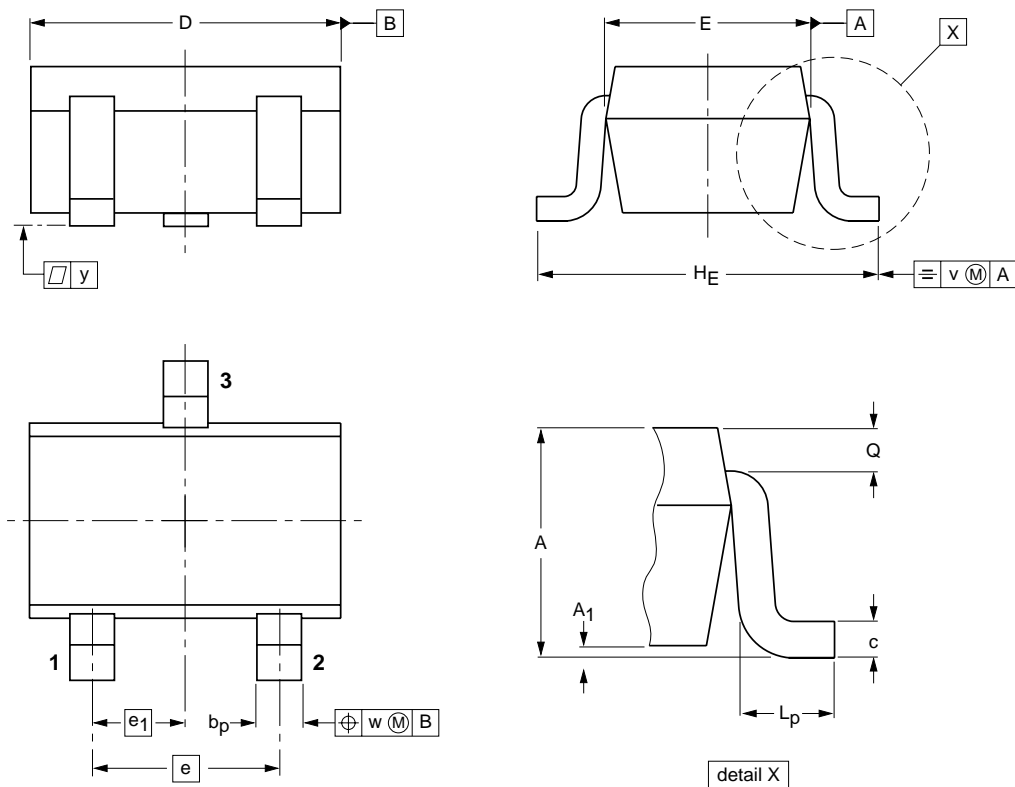
NPN high-voltage transistors

PMSTA42; PMSTA43

PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT323



DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁ max	b _p	c	D	E	e	e ₁	H _E	L _p	Q	v	w
mm	1.1 0.8	0.1	0.4 0.3	0.25 0.10	2.2 1.8	1.35 1.15	1.3	0.65	2.2 2.0	0.45 0.15	0.23 0.13	0.2	0.2

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT323			SC-70			97-02-28

NPN high-voltage transistors

PMSTA42; PMSTA43

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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Printed in The Netherlands

115002/00/02/pp6

Date of release: 1999 May 21

Document order number: 9397 750 05964

